

<b>Form 1449 (Modified)</b>  <b>Information Disclosure Statement By Applicant</b>  (Use Several Sheets if Necessary)	Atty Docket No. UNTYP038	Application No.: New
	Applicant: Rinerson et al. Filing Date Herewith	Group Not Yet Assigned

**U.S. Patent Documents**

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub- class	Filing Date
* HN	A	6,204,139	03/20/01	Liu, et al.	438	385	8/25/1998
* HN	B	6,531,371	03/11/03	Hsu et al.	438	385	6/28/2001

**Other Documents**

Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
HN	C	Beck, A. et al., " <i>Reproducible switching effect in thin oxide films for memory applications</i> ," Applied Physics Letters, Vol. 77, No. 1, 3 July 2000, 139-141.
HN	D	Liu, S.Q., et al., " <i>Electric-pulse-induced reversible resistance change effect in magnetoresistive films</i> ", Applied Physics Letters, Vol. 76, No. 19, 8 May 2000, 2749-2651.
HN	E	Liu, S.Q., et al., " <i>A New Concept For Non-Volatile Memory: Electric-Pulse Induced Reversible Resistance Change Effect In Magnetoresistive Films</i> ", Space Vacuum Epitaxy Center, University of Huston, Huston TX, 7 Pages.
HN	F	Rossel, C. et al., " <i>Electrical current distribution across a metal-insulator-metal structure during bistable switching</i> ," Journal of Applied Physics, Vol. 90, No. 6, 15 September 2001, 2892-2898.
HN	G	Watanabe, Y. et al., " <i>Current-driven insulator-conductor transition and nonvolatile memory in chromium-doped SrTiO<sub>3</sub> single crystals</i> ," Applied Physics Letters, Vol. 78, No. 23, 4 June 2001, 3738-3740.
Examiner	HIEN NGUYEN	
	Date Considered	10/23/05

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.